

HEFEI HEJING ELECTRONICS CO.LTD

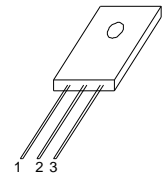
HJ 13003

NPN EPITAXIAL SILICON

TRANSISTOR

Absolute Maximum Ratings (Ta=25)

| Characteristic | Symbol | Rating | Unit |
|-----------------------------|-----------|----------|------|
| Collector-Base Voltage | V_{CB0} | 700 | V |
| Collector-Emitter Voltage | V_{CE0} | 400 | V |
| Emitter-Base Voltage | V_{EB0} | 9 | V |
| Collector Current | I_C | 1 | A |
| Collector Power Dissipation | P_C | 30 | W |
| Junction Temperature | T_j | 150 | |
| Storage Temperature Range | T_{stg} | -55~ 150 | |



1, B 2, C 3, E

TO-126

Electrical Characteristic (Ta=25)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|--------------------------------------|---------------|-------------------------|-----|-----|-----|------|
| Collector-Base Voltage | V_{CB0} | $I_C=1mA$ | 700 | | | V |
| Collector-Emitter Voltage | V_{CE0} | $I_C=10mA$ | 400 | | | V |
| Emitter-Base Voltage | V_{EB0} | $I_E=1mA$ | 9 | | | V |
| DC Current Gain | h_{FE} | $V_{CE}=10V, I_C=0.5A$ | 10 | | 40 | |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C=1A$ $I_B=0.25A$ | | | 1 | V |

h_{FE} Classification: 10~ 15 15~ 20 20~ 25 25~ 30
 30~ 35 35~ 40